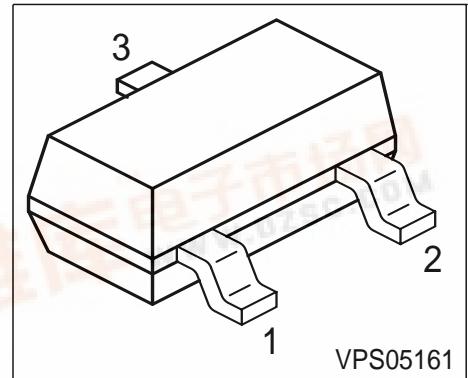




PNP Silicon Switching Transistors

- High DC current gain: 0.1mA to 500 mA
- Low collector-emitter saturation voltage
- Complementary types: BSS79, BSS81 (NPN)



| Type | Marking | Pin Configuration | | | Package |
|--------|---------|-------------------|-------|-------|---------|
| BSS80B | CHs | 1 = B | 2 = E | 3 = C | SOT23 |
| BSS80C | CJs | 1 = B | 2 = E | 3 = C | SOT23 |
| BSS82B | CLs | 1 = B | 2 = E | 3 = C | SOT23 |
| BSS82C | CMs | 1 = B | 2 = E | 3 = C | SOT23 |

Maximum Ratings

| Parameter | Symbol | BSS80 | BSS82 | Unit |
|---|-----------|-------|-------------|------------------|
| Collector-emitter voltage | V_{CEO} | 40 | 60 | V |
| Collector-base voltage | V_{CBO} | | 60 | V |
| Emitter-base voltage | V_{EBO} | | 5 | |
| DC collector current | I_C | | 800 | mA |
| Peak collector current | I_{CM} | | 1 | A |
| Base current | I_B | | 100 | mA |
| Peak base current | I_{BM} | | 200 | |
| Total power dissipation, $T_S = 77^\circ\text{C}$ | P_{tot} | | 330 | mW |
| Junction temperature | T_j | | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | | -65 ... 150 | |

Thermal Resistance

| | | | |
|--|------------|------------|-----|
| Junction - soldering point ¹⁾ | R_{thJS} | ≤ 220 | K/W |
|--|------------|------------|-----|

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

| Parameter | Symbol | Values | | | Unit |
|---|-----------------------------|--------|------|------|------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Collector-emitter breakdown voltage $I_C = 10 \text{ mA}, I_B = 0$ | $V_{(\text{BR})\text{CEO}}$ | 40 | - | - | V |
| | | 60 | - | - | |
| Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$ | $V_{(\text{BR})\text{CBO}}$ | 60 | - | - | |
| Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$ | $V_{(\text{BR})\text{EBO}}$ | 5 | - | - | |
| Collector cutoff current $V_{CB} = 50 \text{ V}, I_E = 0$ | I_{CBO} | - | - | 10 | nA |
| Collector cutoff current $V_{CB} = 50 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$ | I_{CBO} | - | - | 10 | µA |
| Emitter cutoff current $V_{EB} = 3 \text{ V}, I_C = 0$ | I_{EBO} | - | - | 10 | nA |
| DC current gain 1) $I_C = 100 \mu\text{A}, V_{CE} = 10 \text{ V}$ | h_{FE} | 40 | - | - | - |
| | | 75 | - | - | |
| $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$ | $BSS80/82B$ | 40 | - | - | |
| | $BSS80/82C$ | 100 | - | - | |
| $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ | $BSS80/82B$ | 40 | - | - | |
| | $BSS80/82C$ | 100 | - | - | |
| $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ | $BSS80/82B$ | 40 | - | 120 | |
| | $BSS80/82C$ | 100 | - | 300 | |
| $I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$ | $BSS80/82B$ | 40 | - | - | |
| | $BSS80/82C$ | 50 | - | - | |
| Collector-emitter saturation voltage1) $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ | V_{CEsat} | - | - | 0.4 | V |
| $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | - | - | 1.6 | |
| Base-emitter saturation voltage 1) $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ | V_{BEsat} | - | - | 1.3 | |
| $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | - | - | 2.6 | |

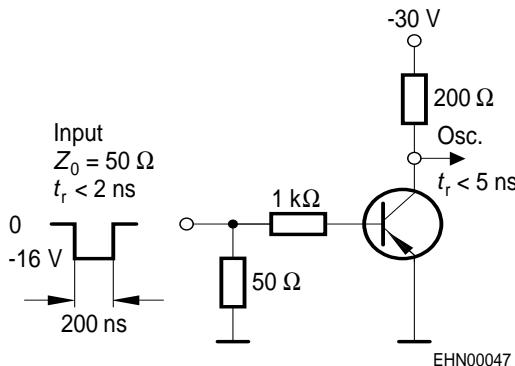
1) Pulse test: $t \leq 300\mu\text{s}, D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

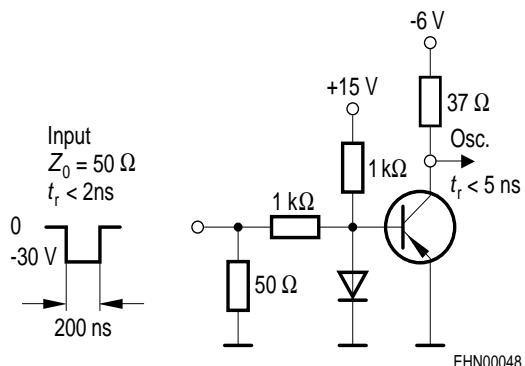
| Parameter | Symbol | Values | | | Unit |
|---|-----------|--------|------|------|------|
| | | min. | typ. | max. | |
| AC Characteristics | | | | | |
| Transition frequency $I_C = 20 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$ | f_T | - | 250 | - | MHz |
| Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$ | C_{cb} | - | 6 | - | pF |
| Delay time $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = 15 \text{ mA}, V_{BE(\text{off})} = 0.5 \text{ V}$ | t_d | - | - | 10 | ns |
| Rise time $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = 15 \text{ mA}, V_{BE(\text{off})} = 0.5 \text{ V}$ | t_r | - | - | 40 | |
| Storage time $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1}=I_{B2} = 15 \text{ mA}$ | t_{stg} | - | - | 80 | |
| Fall time $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1}=I_{B2} = 15 \text{ mA}$ | t_f | - | - | 30 | |

Test circuits

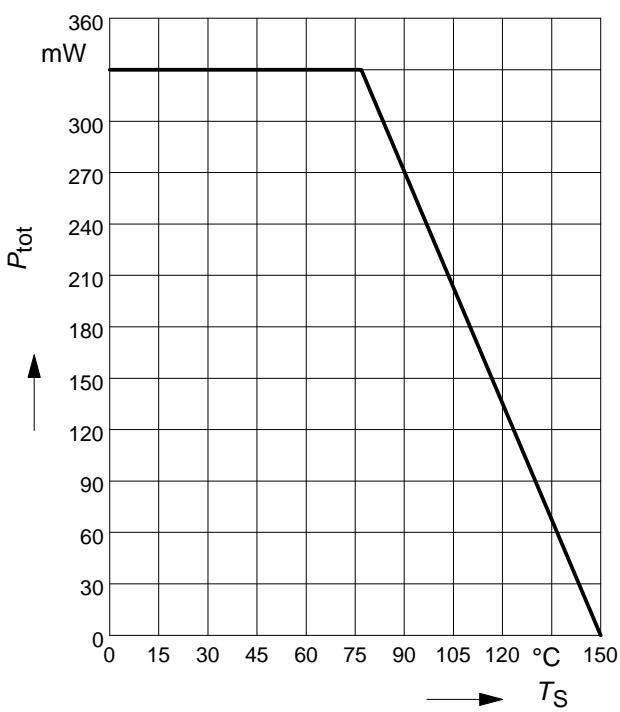
Delay and rise time



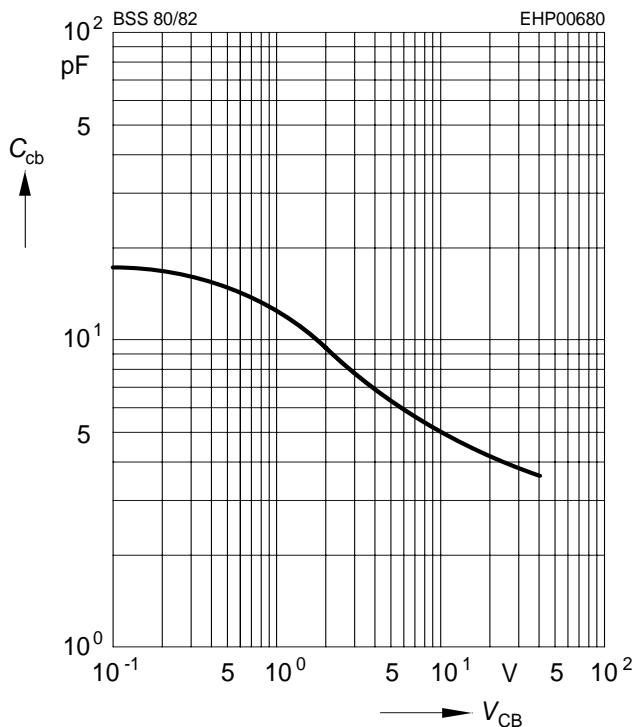
Storage and fall time



Total power dissipation $P_{\text{tot}} = f(T_S)$

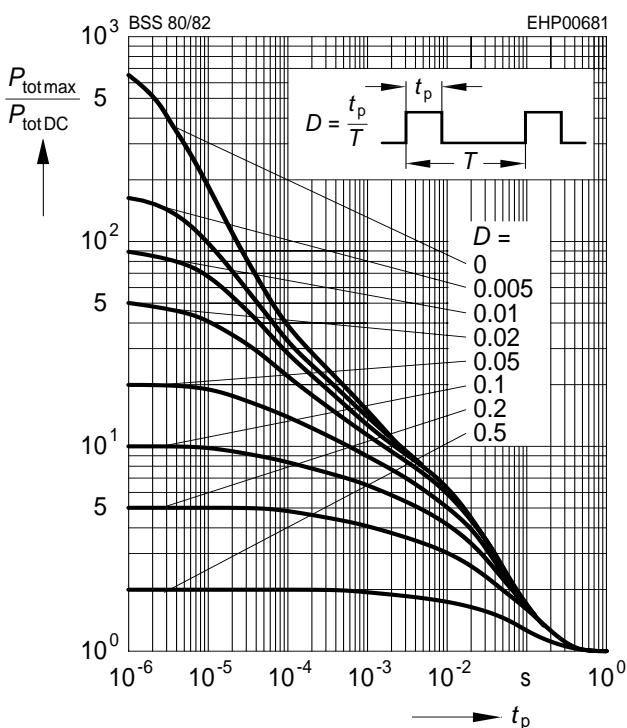


Collector-base capacitance $C_{CB} = f(V_{CB})$
 $f = 1\text{MHz}$



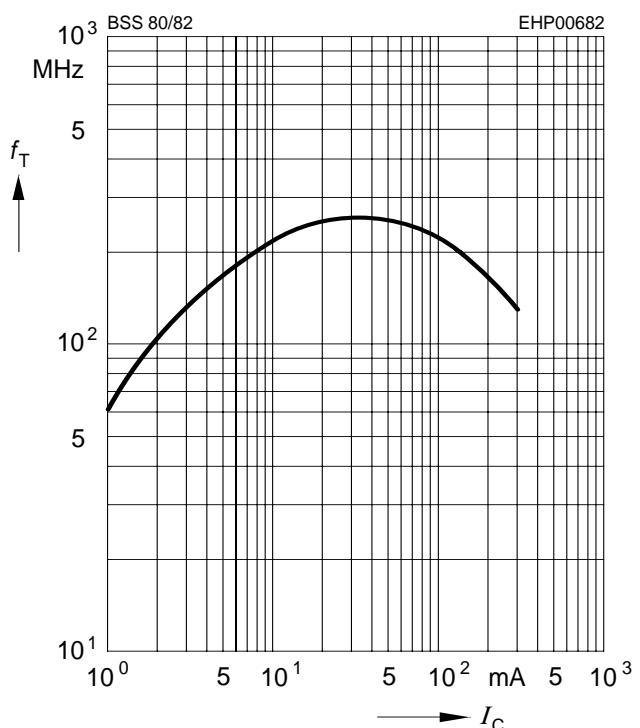
Permissible pulse load

$$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$$

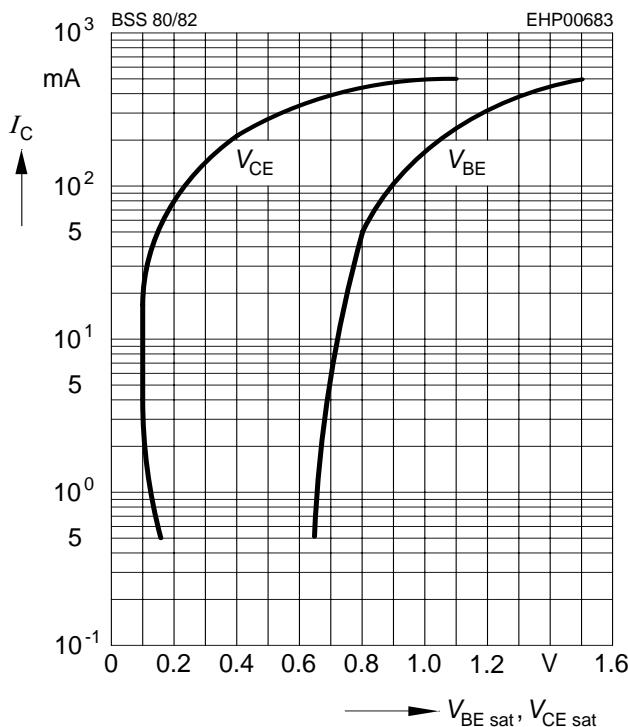


Transition frequency $f_T = f(I_C)$

$$V_{CE} = 20\text{V}$$

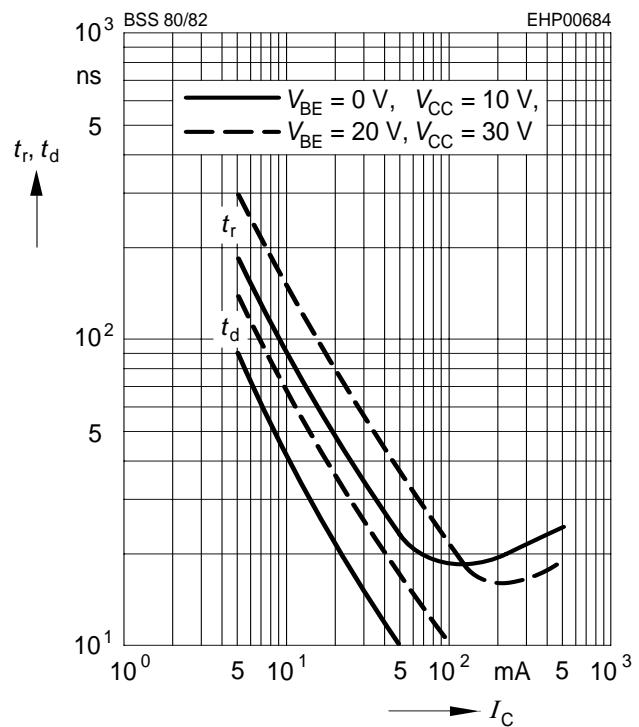


Saturation voltage $I_C = f(V_{BEsat}, V_{CEsat})$
 $h_{FE} = 10$

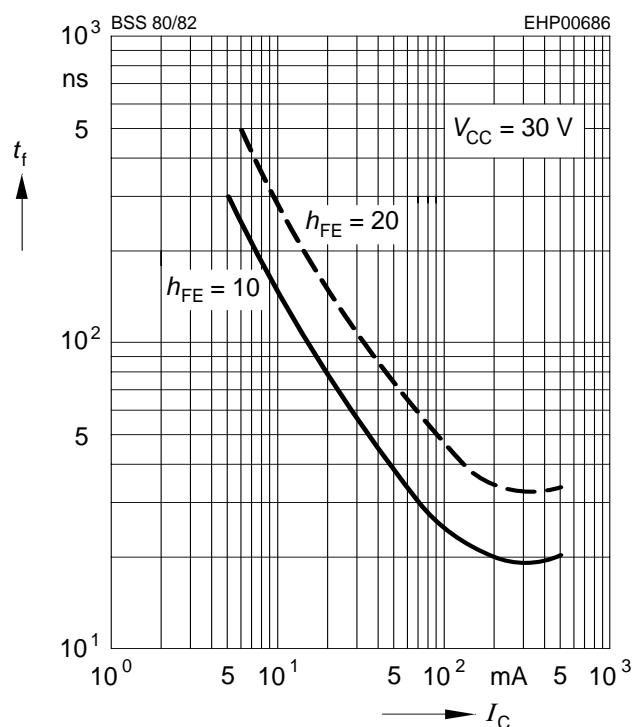
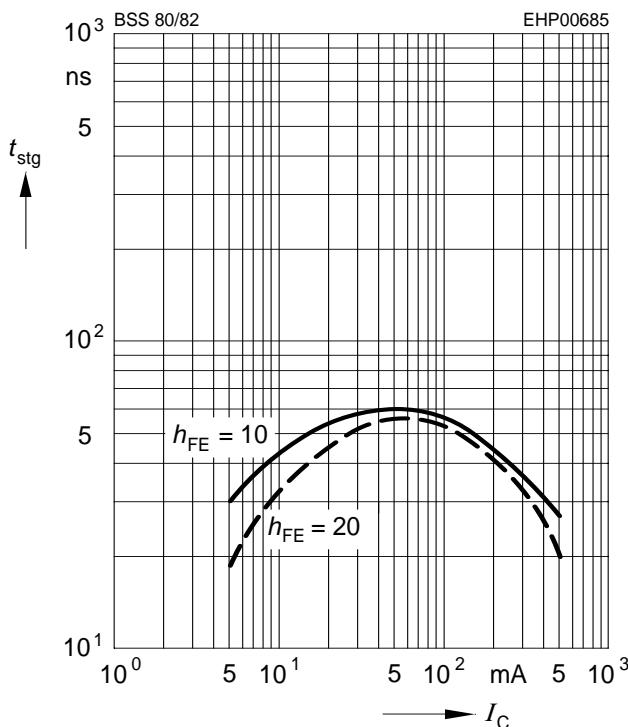


Storage time $t_{stg} = f(I_C)$

Delay time $t_d = f(I_C)$
Rise time $t_r = f(I_C)$



Fall time $t_f = f(I_C)$



DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 10V$

